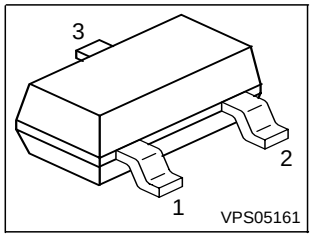
SIPMOS® Small-Signal-Transistor

Features

- P-Channel
- Enhancement mode
- Avalanche rated
- Logic Level
- d*v*/d*t* rated
- Pb-free lead plating; RoHS compliant
- Qualified according to AEC Q101
- Halogen-free according to IEC61249-2-21

Product Summary

Drain source voltage	V_{DS}	-60	V
Drain-source on-state resistance	$R_{DS(on)}$	2	Ω
Continuous drain current	I_D	-0.33	A



Type	Package	Tape and Reel	Marking	Pin 1	PIN 2	PIN 3
BSS 83 P	PG-SOT-23	H6327: 3000pcs/r.	YAs	G	S	D

Maximum Ratings,at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current T_A = 25 °C T_A = 70 °C	I_D	 -0.33 -0.27	A
Pulsed drain current T_A = 25 °C	$I_{D\ puls}$	-1.32	
Avalanche energy, single pulse I_D = -0.33 A , V_{DD} = -25 V, R_{GS} = 25 Ω	E_{AS}	9.5	mJ
Avalanche energy, periodic limited by T_{jmax}	E_{AR}	0.036	
Reverse diode d*v*/d*t* I_S = -0.33 A, V_{DS} = -48 V, d*i*/d*t* = 200 A/µs, T_{jmax} = 150 °C	d*v*/d*t*	6	kV/µs
Gate source voltage	V_{GS}	±20	V
Power dissipation T_A = 25 °C	P_{tot}	0.36	W
Operating and storage temperature	T_j , T_{stg}	-55...+150	°C
IEC climatic category; DIN IEC 68-1		55/150/56	
ESD Class; JESD22-A114-HBM		Class 0	

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - soldering point (Pin 3)	R_{thJS}	-	-	150	K/W
SMD version, device on PCB:	R_{thJA}				
@ min. footprint		-	-	350	
@ 6 cm^2 cooling area [1)]		-	-	300	

Electrical Characteristics, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Drain- source breakdown voltage V_{GS} = 0 V, I_D = -250 µA	$V_{(BR)DSS}$	-60	-	-	V
Gate threshold voltage, V_{GS} = V_{DS} I_D = -80 µA	$V_{GS(th)}$	-1	-1.5	-2	
Zero gate voltage drain current	I_{DSS}				µA
V_{DS} = -60 V, V_{GS} = 0 V, T_j = 25 °C		-	-0.1	-1	
V_{DS} = -60 V, V_{GS} = 0 V, T_j = 125 °C		-	-10	-100	
Gate-source leakage current V_{GS} = -20 V, V_{DS} = 0 V	I_{GSS}	-	-10	-100	nA
Drain-source on-state resistance V_{GS} = -4.5 V, I_D = -0.27 A	$R_{DS(on)}$	-	2	3	Ω
Drain-source on-state resistance V_{GS} = -10 V, I_D = -0.33 A	$R_{DS(on)}$	-	1.4	2	

[1]Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm^2 (one layer, 70 µm thick) copper area for drain connection. PCB is vertical without blown air.

Electrical Characteristics, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Dynamic Characteristics					
Transconductance $V_{DS}\geq 2*I_D*R_{DS(on)max}$, I_D = -0.27 A	g_{fs}	0.24	0.47	-	S
Input capacitance V_{GS} = 0 V, V_{DS} = -25 V, f = 1 MHz	C_{iss}	-	62	78	pF
Output capacitance V_{GS} = 0 V, V_{DS} = -25 V, f = 1 MHz	C_{oss}	-	19	24	
Reverse transfer capacitance V_{GS} = 0 V, V_{DS} = -25 V, f = 1 MHz	C_{rss}	-	7	9	
Turn-on delay time V_{DD} = -30 V, V_{GS} = -4.5 V, I_D = -0.27 A, R_G = 43 Ω	$t_{d(on)}$	-	23	35	ns
Rise time V_{DD} = -30 V, V_{GS} = -4.5 V, I_D = -0.27 A, R_G = 43 Ω	t_r	-	71	106	
Turn-off delay time V_{DD} = -30 V, V_{GS} = -4.5 V, I_D = -0.27 A, R_G = 43 Ω	$t_{d(off)}$	-	56	70	
Fall time V_{DD} = -30 V, V_{GS} = -4.5 V, I_D = -0.27 A, R_G = 43 Ω	t_f	-	61	76	

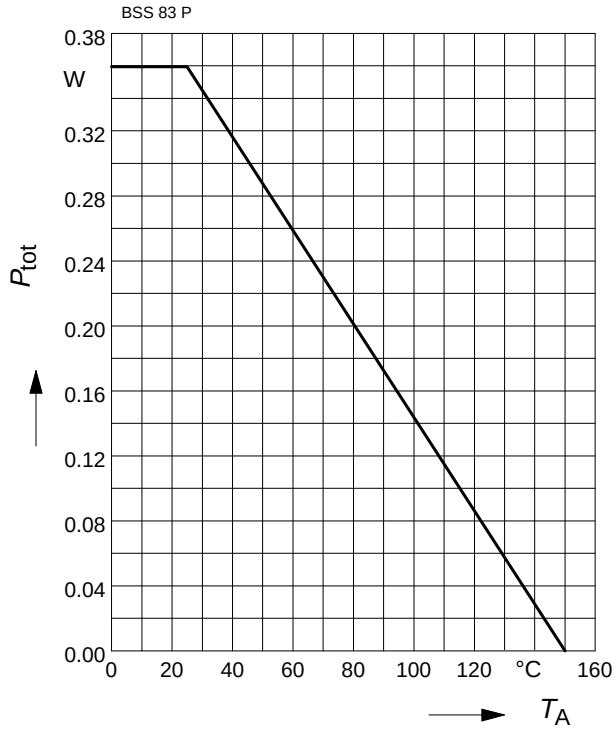
Electrical Characteristics, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Dynamic Characteristics					
Gate to source charge V_{DD} = -48 V, I_D = -0.33 A	Q_{gs}	-	0.12	0.18	nC
Gate to drain charge V_{DD} = -48 , I_D = -0.33 A	Q_{gd}	-	1.1	1.65	
Gate charge total V_{DD} = -48 V, I_D = -0.33 A, V_{GS} = 0 to -10 V	Q_g	-	2.38	3.57	
Gate plateau voltage V_{DD} = -48 V , I_D = -0.33 A	$V_{(plateau)}$	-	-2.94	-	V

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Reverse Diode					
Inverse diode continuous forward current T_A = 25 °C	I_S	-	-	-0.33	A
Inverse diode direct current,pulsed T_A = 25 °C	I_{SM}	-	-	-1.32	
Inverse diode forward voltage V_{GS} = 0 V, I_F = -0.33	V_{SD}	-	-0.84	-1.1	V
Reverse recovery time V_R = -30 V, I_F=I_S , di_F/dt = 80 A/µs	t_{rr}	-	59.4	89	ns
Reverse recovery charge V_R = -30 V, I_F=I_S , di_F/dt = 80 A/µs	Q_{rr}	-	37.5	56	nC

Power Dissipation

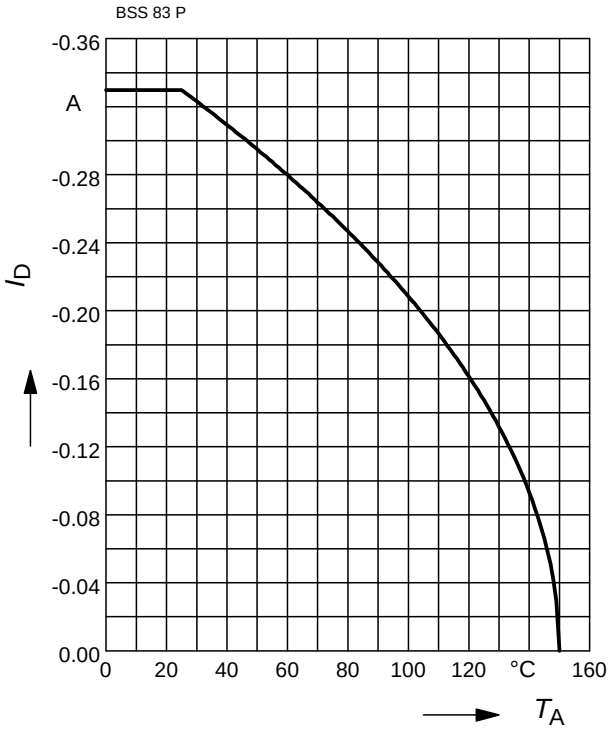
$P_{tot} = f(T_A)$



Drain current

$I_D = f(T_A)$

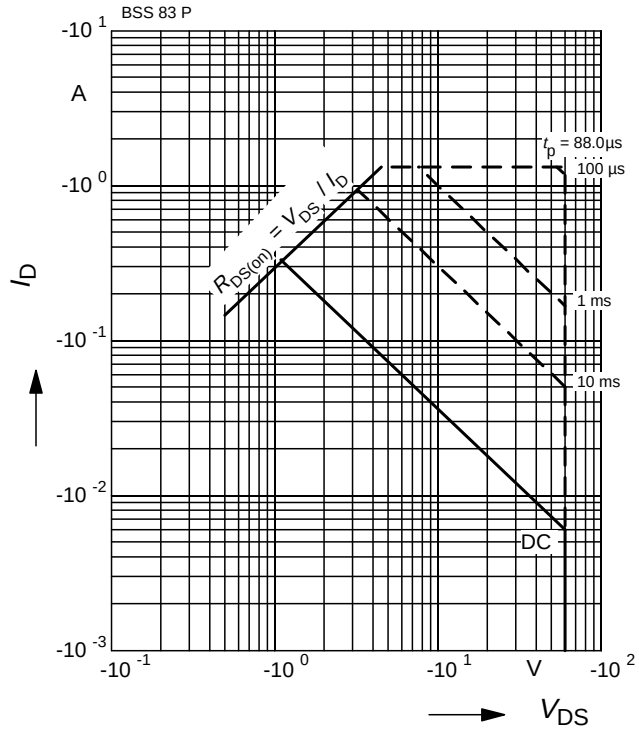
parameter: $V_{GS} \geq 10$ V



Safe operating area

$I_D = f(V_{DS})$

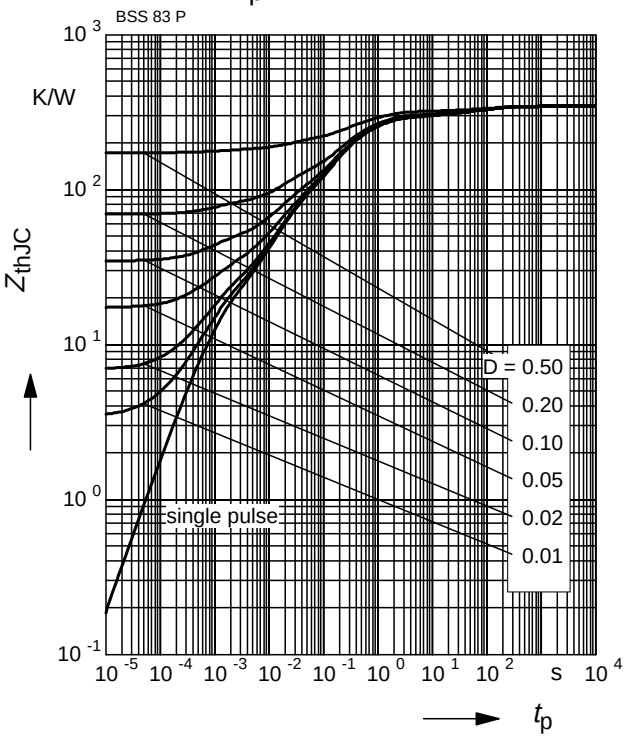
parameter : $D = 0$, $T_A = 25$ °C



Transient thermal impedance

$Z_{thJC} = f(t_p)$

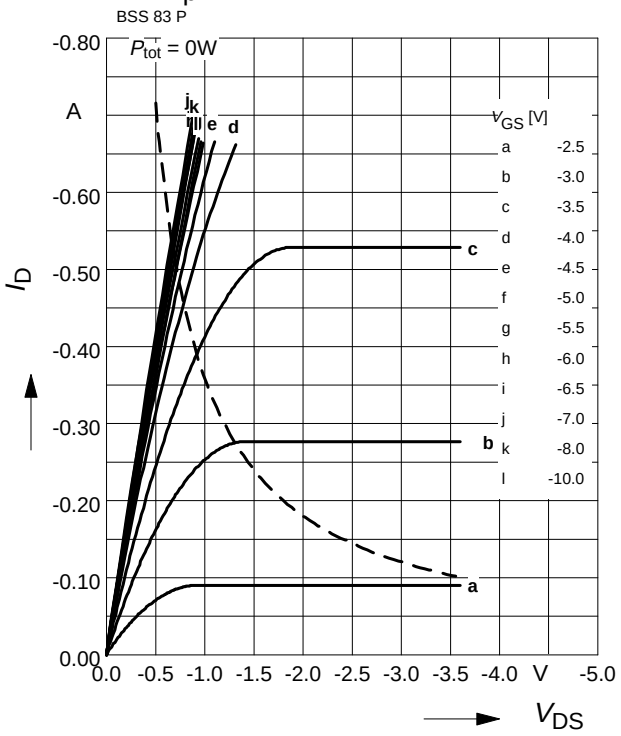
parameter : $D = t_p / T$



Typ. output characteristic

$I_D = f(V_{DS})$; T_j=25°C

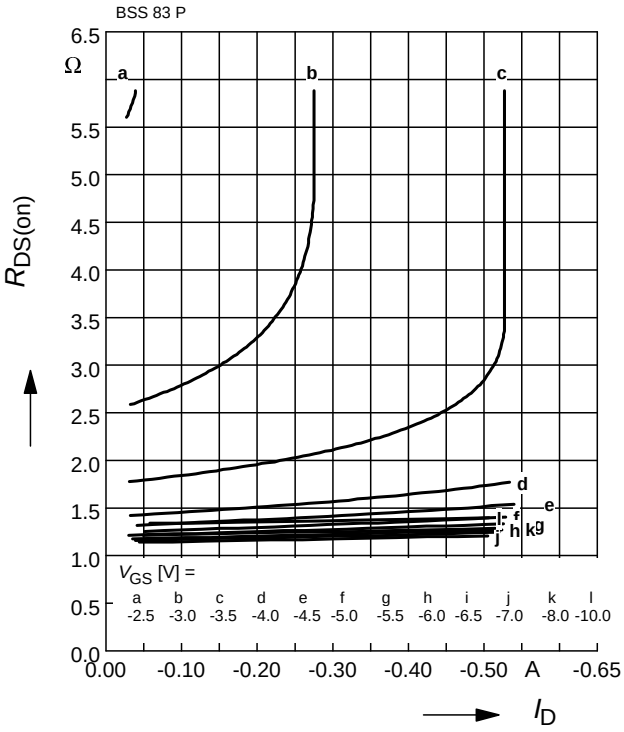
parameter: t_p = 80 µs



Typ. drain-source-on-resistance

$R_{DS(on)} = f(I_D)$

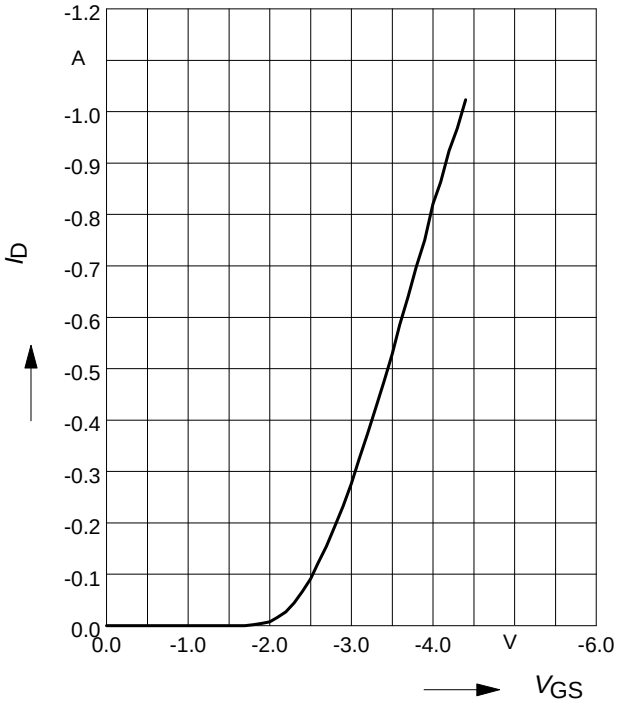
parameter: V_{GS}



Typ. transfer characteristics $I_D = f(V_{GS})$

$V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$

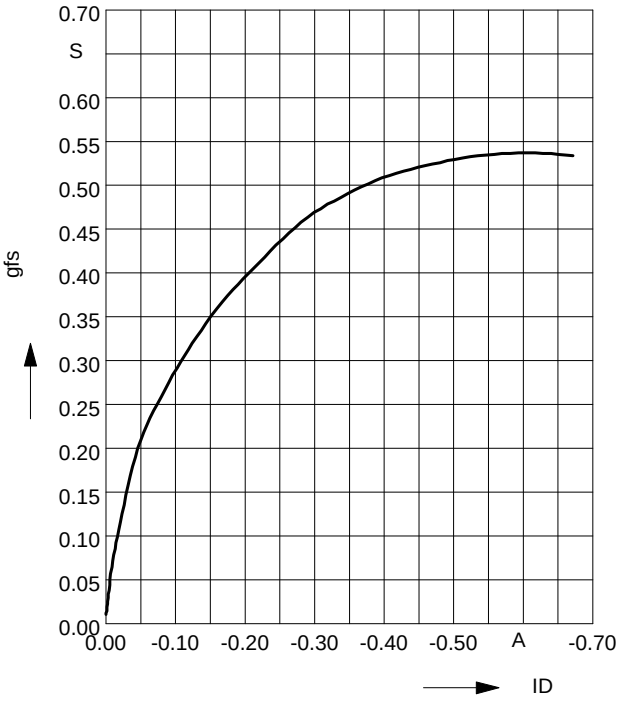
parameter: t_p = 80 µs



Typ. forward transconductance

g_{fs} = f(I_D); T_j=25°C

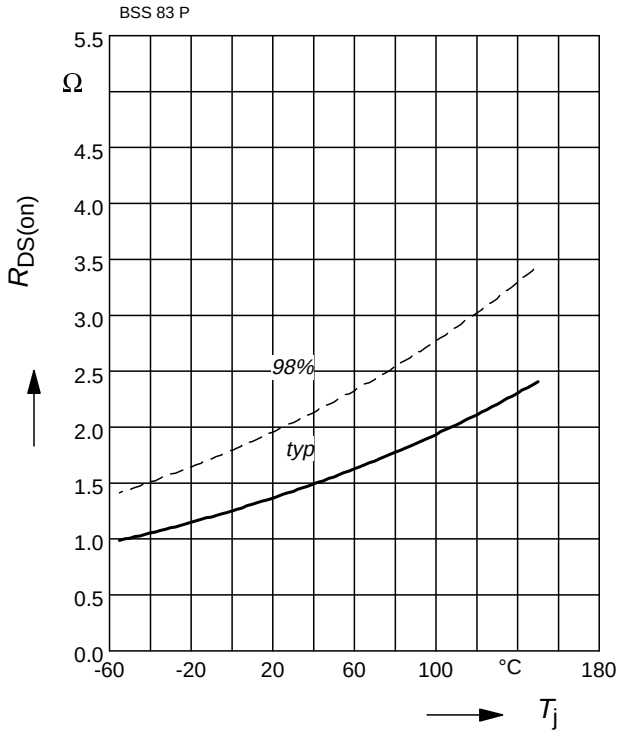
parameter: g_{fs}



Drain-source on-state resistance

$R_{DS(on)} = f(T_j)$

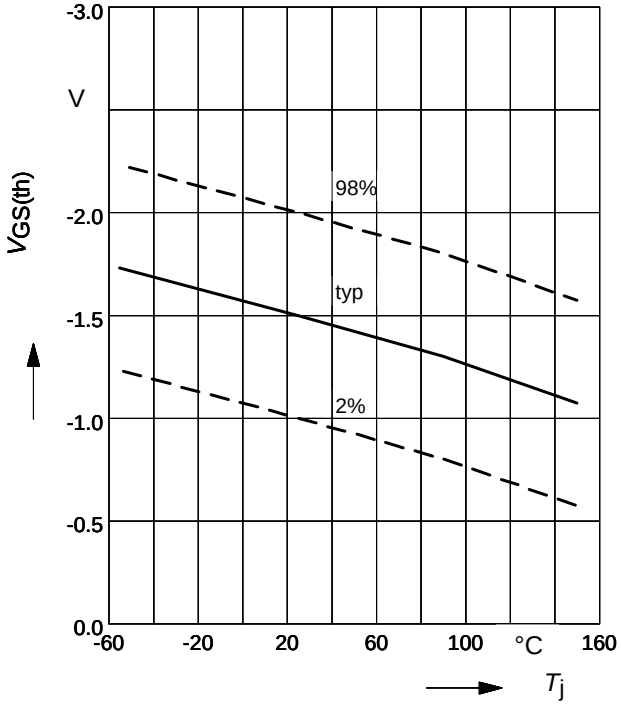
parameter : I_D = -0.33 A, V_{GS} = -10 V



Gate threshold voltage

$V_{GS(th)} = f(T_j)$

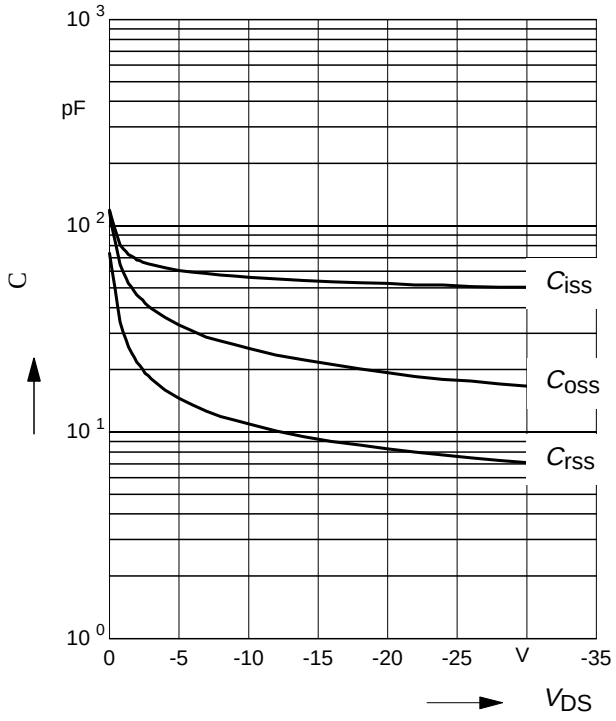
parameter: $V_{GS} = V_{DS}$, I_D = -80 µA



Typ. capacitances

$C = f(V_{DS})$

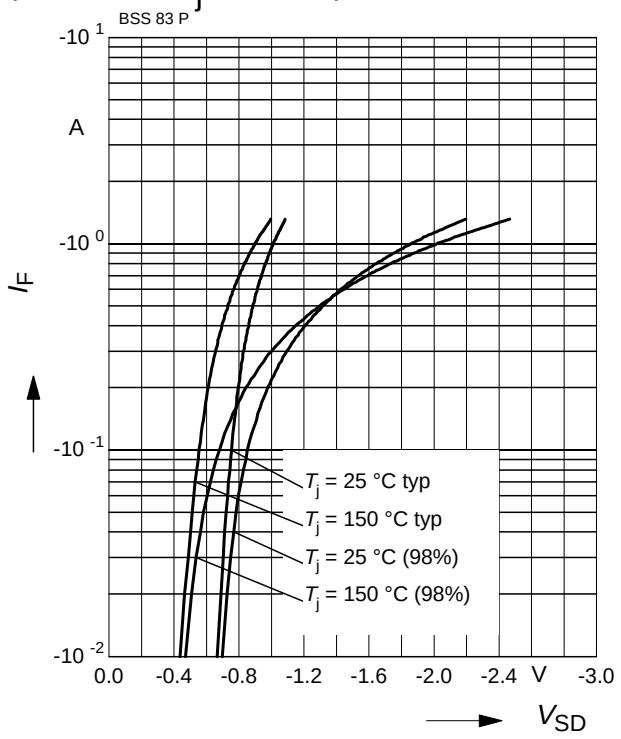
parameter: V_{GS}=0V, f=1 MHz



Forward characteristics of reverse diode

$I_F = f(V_{SD})$

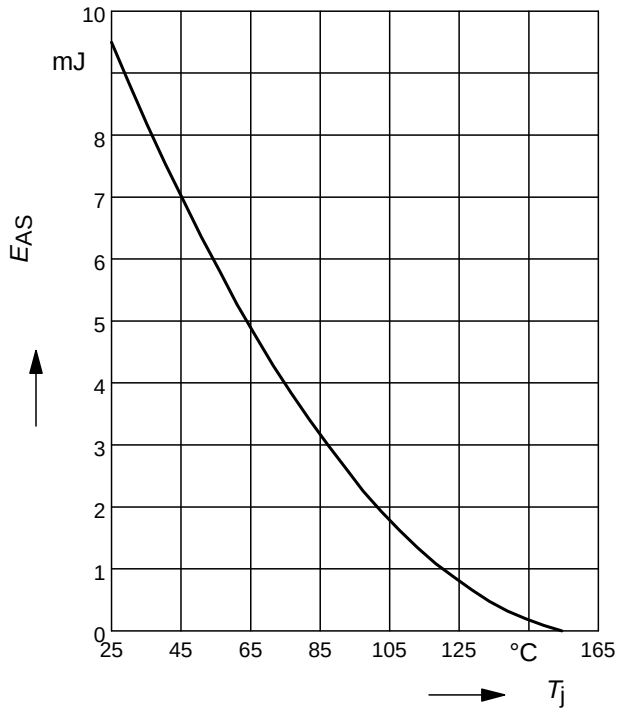
parameter: T_j , tp = 80 µs



Avalanche energy

$E_{AS} = f(T_j)$

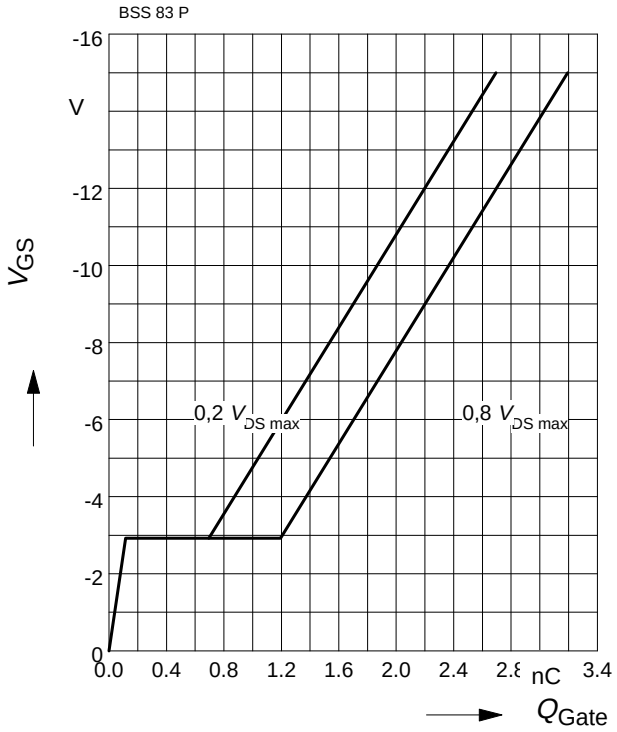
para.: I_D = -0.33 A , V_{DD} = -25 V, R_{GS} = 25



Typ. gate charge

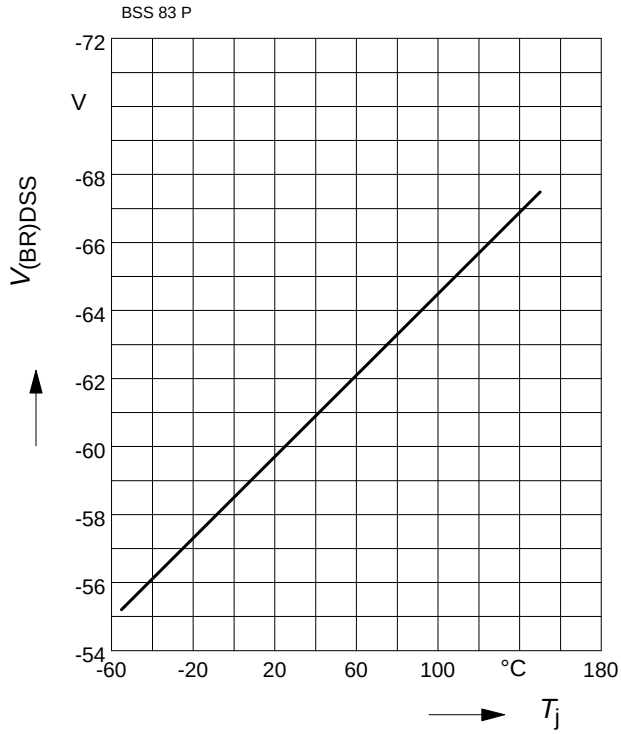
$V_{GS} = f\ (Q_{Gate})$

parameter: I_D = -0.33 A pulsed



Drain-source breakdown voltage

$V_{(BR)DSS} = f(T_j)$



Published by
Infineon Technologies AG
81726 Munich, Germany

Legal Disclaimer
The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

Information
For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office (www.infineon.com).

Warnings
Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office.
Infineon Technologies components may be used in life-support devices or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.